

Product Overview

This RHA level 2N3057A NPN Silicon Transistor device is military qualified up to a JANSR level for high-reliability applications requiring a radiation hardened device per MIL-PRF-19500/391. Microchip also offers numerous other products to meet higher and lower power voltage regulation applications.

Qualified Levels:

- JANSE
- JANSK
- JANSU
- JANSM
- JANS D
- JANSP
- JANS L
- JANSR

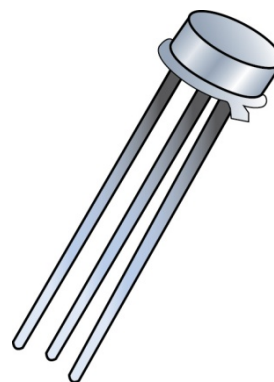
Features

- JEDEC registered 2N3057
- RHA level JAN qualifications per MIL-PRF-19500/391 (see [Part Nomenclature](#) for all options)

Applications/Benefits

- Low profile metal TO-46 leaded package
- Light weight
- General-purpose switching and amplifier applications
- Military and high-reliability applications

Figure 1. TO-46 (TO-206AB) Package



Also available in:

TO-39 (TO-205AD)

(leaded)

[JANS_2N3019, 2N3019S](#)

TO-18 (TO-206AA)

(leaded)

[JANS_2N3700](#)

UB package

(surface mount)

[JANS_2N3700UB](#)

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1. Maximum Ratings

Table 1-1. Maximum Ratings at 25 °C Unless Otherwise Noted

Parameters/Test Conditions		Symbol	Value	Unit
Junction and storage temperature		T_J and T_{STG}	-65 to +200	°C
Thermal impedance junction-to-ambient		$R_{\theta JA}$	325	°C/W
Thermal impedance junction-to-case		$R_{\theta JC}$	80	°C/W
Collector-Emitter voltage		V_{CEO}	80	V
Collector-Base voltage		V_{CBO}	140	V
Emitter-Base voltage		V_{EBO}	7.0	V
Collector current		I_C	1.0	A
Total power dissipation:	at $T_A = +25\text{ °C}$ ¹	P_D	0.5	W
	at $T_C = +25\text{ °C}$ ²		1.8	

Notes:

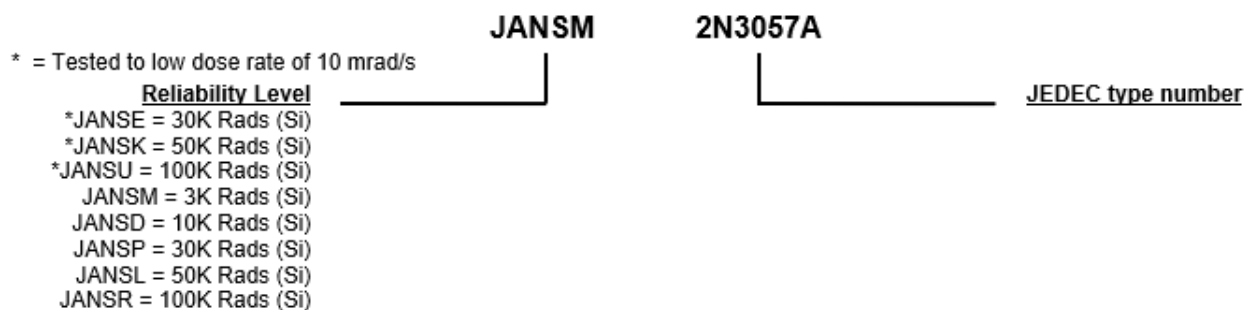
1. Derate linearly 2.3 mW/°C for $T_A \geq +25\text{ °C}$
2. Derate linearly 10.3 mW/°C for $T_C \geq +25\text{ °C}$

1.1 Mechanical Packaging

- Case: Nickel plated kovar, glass seals
- Terminals: Gold over nickel plated kovar leads. Solder dip (Sn63/Pb37) available upon request.
- Marking: Part number, date code, manufacturer's ID and serial number
- Weight: Approximately 0.234 grams
- See [Package Dimensions](#).

2. Part Nomenclature

Figure 2-1. Part Nomenclature



2.1 Symbols and Definitions

Table 2-1. Symbols and Definitions

Symbol	Definition
f	Frequency
I _B	Base current (DC)
I _E	Emitter current (DC)
T _A	Ambient temperature
T _C	Case temperature
V _{CB}	Collector to base voltage (DC)
V _{CE}	Collector to emitter voltage (DC)
V _{EB}	Emitter to base voltage (DC)

3. Electrical Characteristics

Table 3-1. Electrical Characteristics at 25 °C Unless Otherwise Stated

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Off Characteristics				
Collector-Emitter breakdown current $I_C = 30 \text{ mA}$	$V_{(BR)CEO}$	80	—	V
Collector-Base cutoff current $V_{CB} = 140\text{V}$	I_{CBO}	—	10	μA
Emitter-Base cutoff current $V_{EB} = 7\text{V}$	I_{EBO1}	—	10	μA
Collector-Emitter cutoff current $V_{CE} = 90\text{V}$	I_{CES}	—	10	ηA
Emitter-Base cutoff current $V_{EB} = 5.0\text{V}$	I_{EBO2}	—	10	ηA
On Characteristics				
Forward-Current transfer ratio $I_C = 150 \text{ mA}, V_{CE} = 10\text{V}$ $I_C = 0.1 \text{ mA}, V_{CE} = 10\text{V}$ $I_C = 10 \text{ mA}, V_{CE} = 10\text{V}$ $I_C = 500 \text{ mA}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{A}, V_{CE} = 10\text{V}$	h_{FE}	100 50 90 50 15	300 300 — 300 —	—
Collector-Emitter saturation voltage $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$V_{CE(sat)}$	—	0.2 0.5	V
Base-Emitter saturation voltage $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	$V_{BE(sat)}$	—	1.1	V

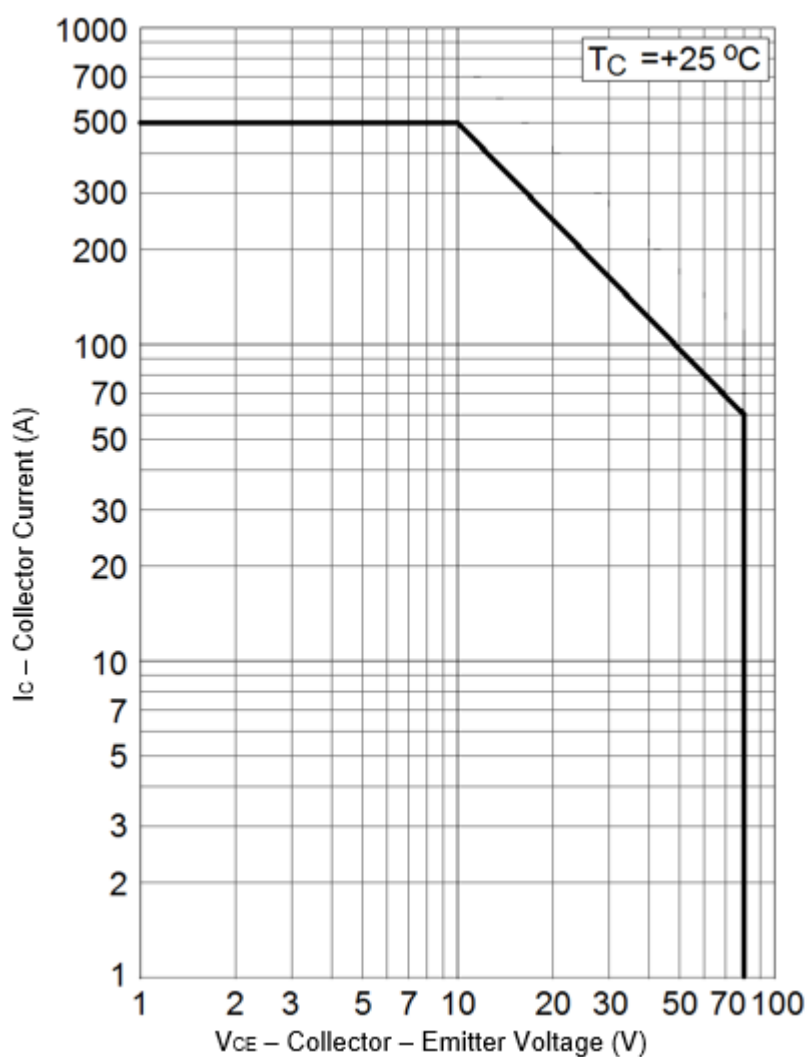
Table 3-2. Dynamic Characteristics

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal short-circuit forward current transfer ratio $I_C = 1.0 \text{ mA}, V_{CE} = 5.0\text{V}, f = 1.0 \text{ kHz}$	h_{fe}	80	400	—
Magnitude of small-signal short-circuit forward current transfer ratio $I_C = 50 \text{ mA}, V_{CE} = 10\text{V}, f = 20 \text{ MHz}$	$ h_{fe} $	5.0	20	—
Output capacitance $V_{CB} = 10\text{V}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{obo}	—	12	pF
Input capacitance $V_{EB} = 0.5\text{V}, I_C = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{ibo}	—	60	pF

Table 3-3. Safe Operation Area (See the Following SOA Graph and [MIL-STD-750, Method 3053](#))

DC Tests	
$T_C = 25\text{ }^{\circ}\text{C}$, 1 cycle, $t = 10\text{ ms}$	
Test 1 2N3057A	$V_{CE} = 10\text{V}$ $I_C = 180\text{ mA}$
Test 2 2N3057A	$V_{CE} = 40\text{V}$ $I_C = 45\text{ mA}$
Test 3 2N3057A	$V_{CE} = 80\text{V}$ $I_C = 22.5\text{ mA}$

Figure 3-1. Maximum Safe Operating Area¹



Note:

1. Pulse Test: Pulse Width = 300 μs , duty cycle $\leq 2.0\%$.

Table 3-4. Post Radiation Electrical Characteristics

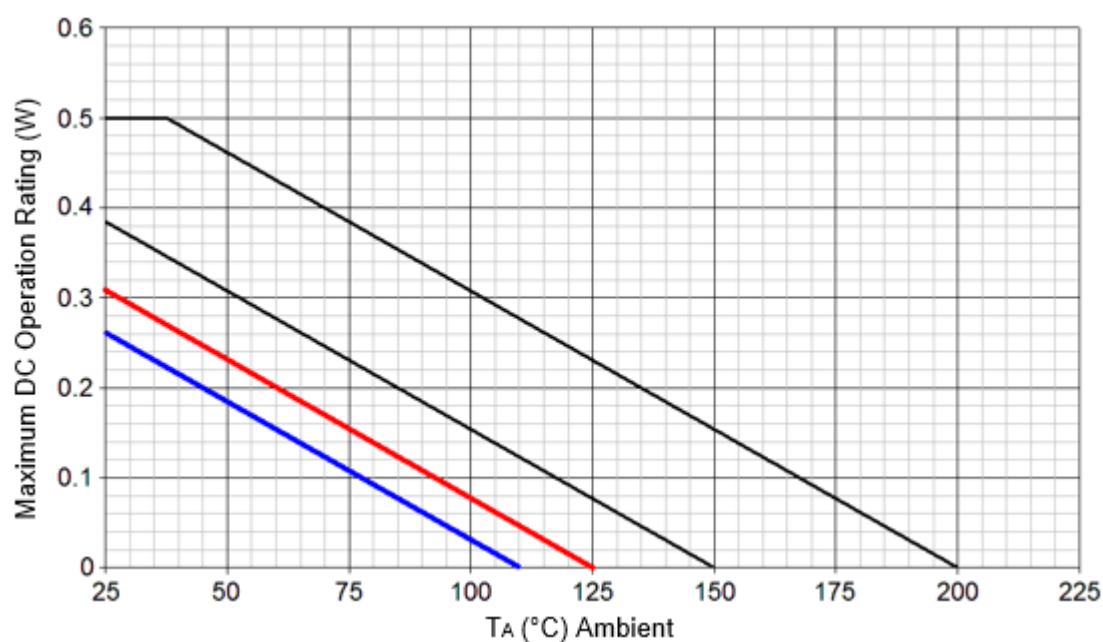
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to base cutoff current $V_{CB} = 140V$	I_{CBO}	—	20	μA
Emitter to base cutoff current $V_{EB} = 7V$	I_{EBO}	—	20	μA
Collector to emitter breakdown voltage $I_C = 30\text{ mA}$	$V_{(BR)CEO}$	80	—	V
Collector-Emitter cutoff current $V_{CE} = 90V$	I_{CES}	—	20	ηA
Emitter-Base cutoff current $V_{EB} = 5.0V$	I_{EBO}	—	20	ηA
Forward-Current transfer ratio ¹ $I_C = 150\text{ mA}, V_{CE} = 10V$ $I_C = 0.1\text{ mA}, V_{CE} = 10V$ $I_C = 10\text{ mA}, V_{CE} = 10V$ $I_C = 500\text{ mA}, V_{CE} = 10V$ $I_C = 1\text{ A}, V_{CE} = 10V$	$[h_{FE}]$	[50] [25] [45] [25] [7.5]	300 300 — 300 —	—
Collector-Emitter saturation voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CE(sat)}$	—	0.23 0.58	V
Base-Emitter saturation voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{BE(sat)}$	—	1.27	V

Note:

1. See method 1019 of MIL-STD-750 for how to determine $[h_{FE}]$ by first calculating the delta ($1/h_{FE}$) from the pre- and post-radiation h_{FE} . Notice the $[h_{FE}]$ is not the same as h_{FE} and cannot be measured directly. The $[h_{FE}]$ value can never exceed the pre-radiation minimum h_{FE} that it is based upon.

4. Graphs

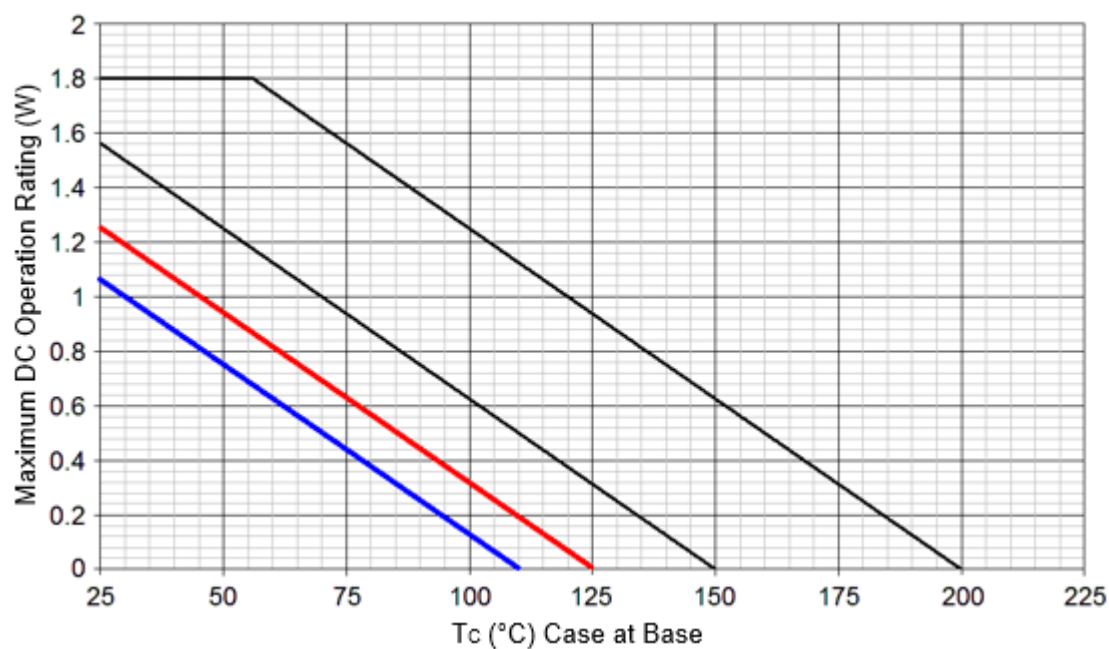
Figure 4-1. Temperature-Power Derating ($R_{\Theta JA}$)¹



Note:

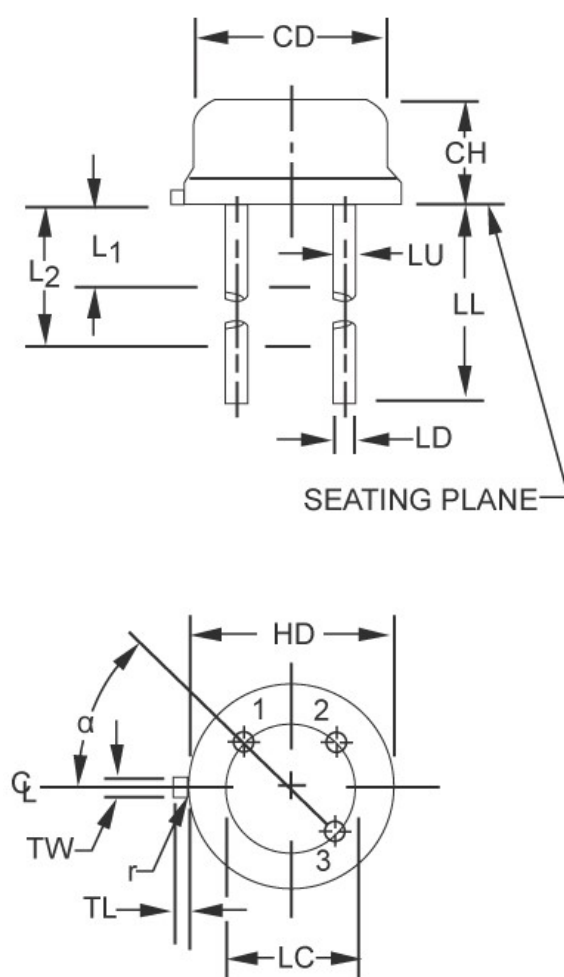
1. Leads = 0.125 inch (3.175 mm)

Figure 4-2. Temperature-Power Derating ($R_{\Theta JS}$)



5. Package Dimensions

Figure 5-1. Package Dimensions



Symbol	Dimensions				Note
	Inches		Millimeters		
	Min.	Max.	Min.	Max.	
CD	0.178	0.195	4.52	4.95	—
CH	0.065	0.085	1.65	2.16	—
HD	0.209	0.230	5.31	5.84	—
LC	0.100 TP		2.54 TP		6
LD	0.016	0.021	0.41	0.53	7
LL	0.500	1.750	12.70	44.45	7
LU	0.016	0.019	0.41	0.48	7
L1	—	0.050	—	1.27	7
L2	0.250	—	6.35	—	7
TL	0.028	0.048	0.71	1.22	3

.....continued

.....continued

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min.	Max.	Min.	Max.	
TW	0.036	0.046	0.91	1.17	2
r	—	0.007	—	0.18	10, 11
α	45° TP		45° TP		6

Notes:

1. Dimension are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of 0.011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Leads at gauge plane 0.054 +0.001 -0.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within 0.007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
6. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. The diameter is uncontrolled in L₁ and beyond LL minimum.
7. All three leads
8. The collector shall be internally connected to the case.
9. Dimension r (radius) applies to both inside corners of tab.
10. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
11. Lead 1 = emitter, lead 2 = base, lead 3 = collector

6. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Revision	Date	Description
A	06/2024	Document was converted to Microchip template. Previous Microsemi literature number T4-LDS-0262 was replaced with DS00005462A.

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